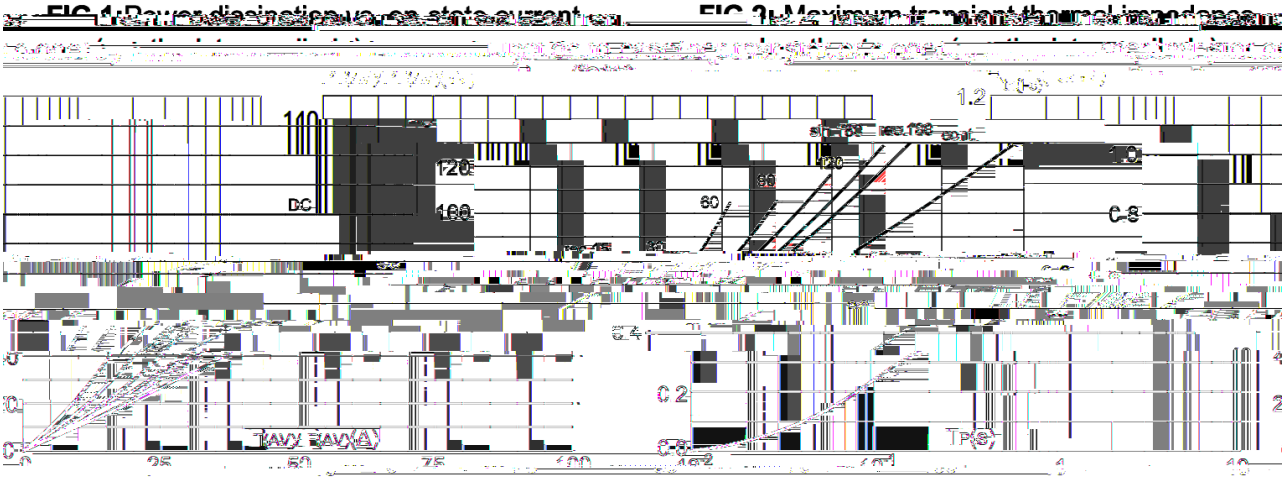
	℃			

	℃					
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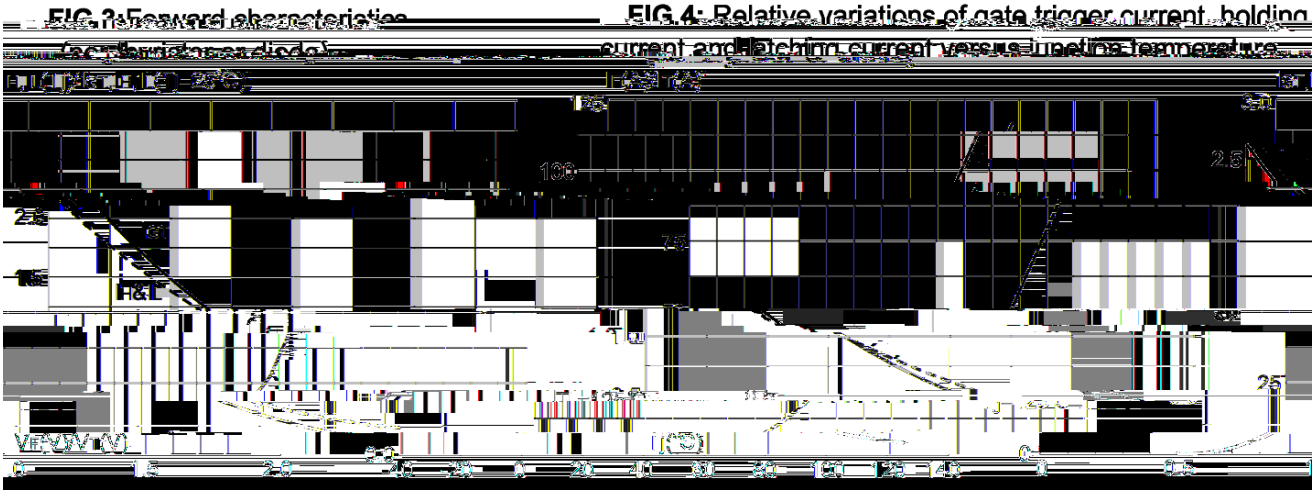


FIG.5 Gate trigger characteristics

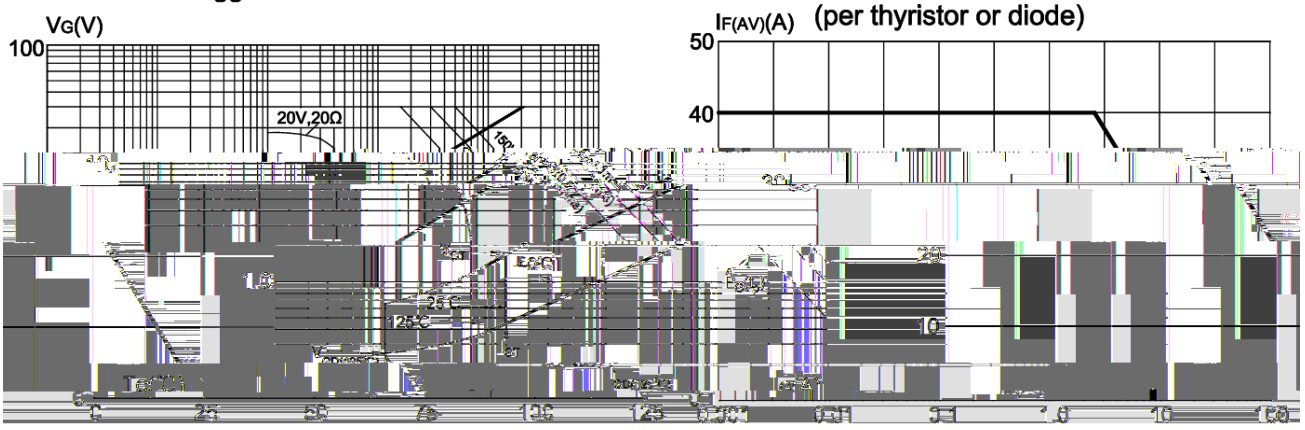
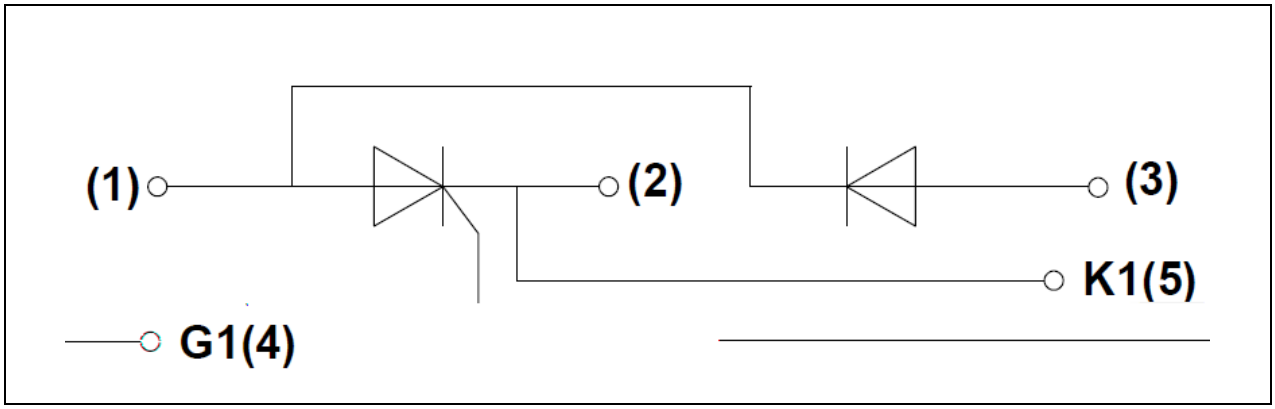
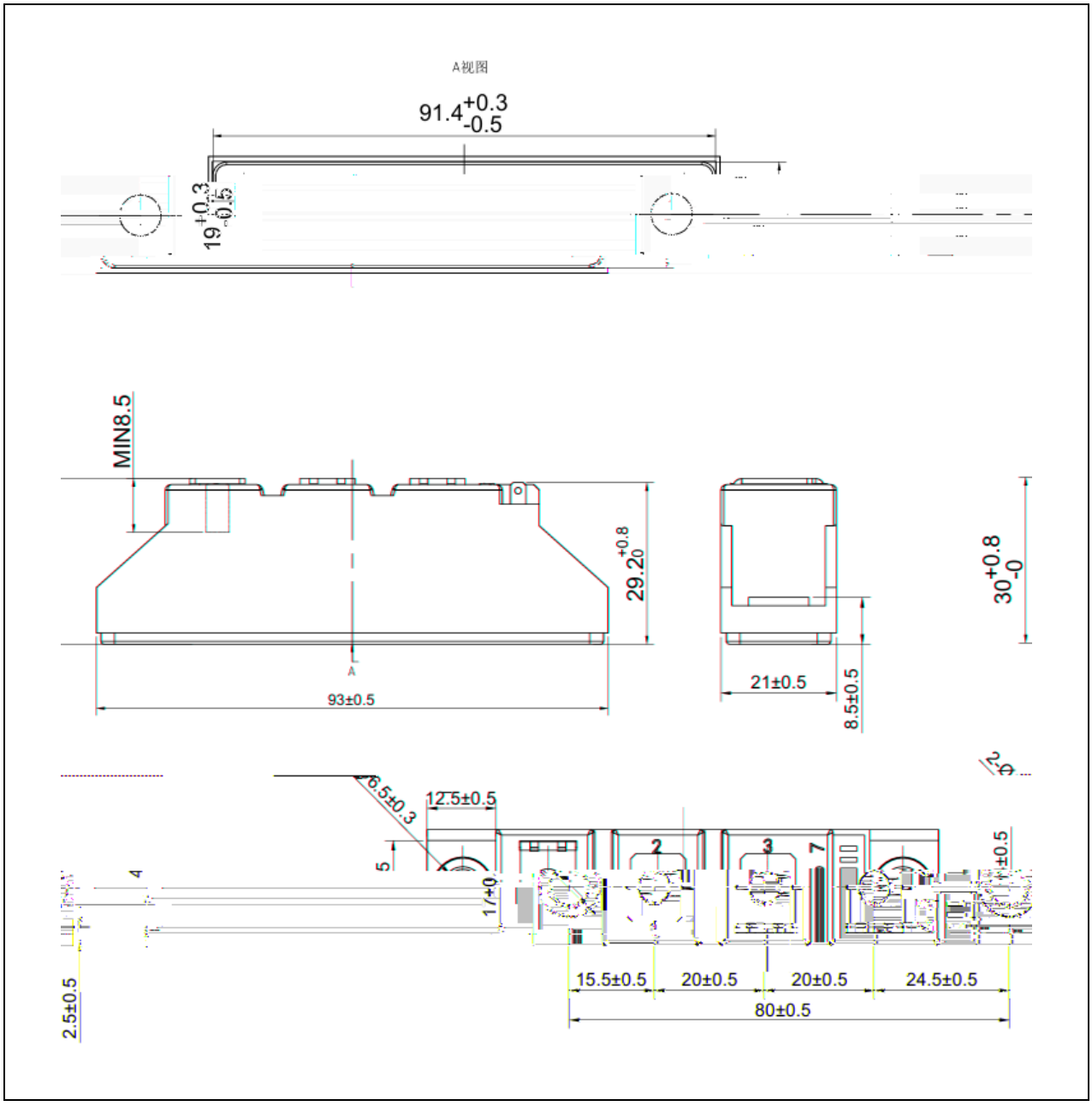


FIG.6: Forward current vs. case temperature (per thyristor or diode)


(1)
(2)
(3)
K1(5)
G1(4)


A视图
91.4+0.3 -0.5
19+0.3 -0.5
MIN8.5
29.20+0.8
93±0.5
21±0.5
8.5±0.5
30+0.8 -0
6.5±0.3
12.5±0.5
5
1/+0
2
3
7
±0.5
4
2.5±0.5
15.5±0.5
20±0.5
20±0.5
24.5±0.5
80±0.5